RGS00TS65HR

650V 50A Field Stop Trench IGBT

Datasheet

V _{CES}	650V
I _{C (100°C)}	50A
V _{CE(sat) (Typ.)}	1.65V
P_{D}	326W



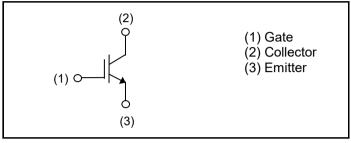
Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Short Circuit Withstand Time 8µs
- 3) Qualified to AEC-Q101
- 4) Pb free Lead Plating; RoHS Compliant

Application

Heater for Automotive

●Inner Circuit



Packaging Specifications

	Packaging	Tube			
	Reel Size (mm)	-			
Tuno	Tape Width (mm)	-			
Type Basic Ordering Unit (pcs)	450				
	Packing Code	C11			
	Marking	RGS00TS65			

● **Absolute Maximum Ratings** (at T_C = 25°C unless otherwise specified)

Parameter Collector - Emitter Voltage		Symbol	Value	Unit V
		V _{CES}	650	
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	T _C = 25°C	I _C	88	Α
	T _C = 100°C	I _C	50	Α
Pulsed Collector Current	ulsed Collector Current		150	Α
Power Dissipation	T _C = 25°C	P _D	326	W
	T _C = 100°C	P _D	163	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiailletei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	ı	0.46	°C/W

●IGBT Electrical Characteristics (at T_i = 25°C unless otherwise specified)

Parameter Syn	Cymbol	Conditions	Values			Unit
	Symbol Conditions –		Min.	Тур.	Max.	Ullit
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
		$V_{CE} = 650V, V_{GE} = 0V,$				
Collector Cut - off Current	I _{CES}	$T_j = 25^{\circ}C$ $Tj = 175^{\circ}C^{*2}$	-	-	10	μΑ
		Tj = 175°C ^{*2}		ı	5	mA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	1	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 2.5mA$	5.0	6.0	7.0	V
		$I_C = 50A, V_{GE} = 15V,$				
Collector - Emitter Saturation Voltage	V _{CE(sat)}	T _j = 25°C	-	1.65	2.10	V
		T _j = 175°C	-	2.15	-	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Davamatas	Symbol	Conditions	Values			Unit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V,	-	1568	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$,	-	134	-	pF
Reverse transfer Capacitance	C_{res}	f = 1MHz	-	23	-	
Total Gate Charge	Q_g	V _{CE} = 300V,	-	58	-	
Gate - Emitter Charge	Q_ge	I _C = 50A,	-	15	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	24	-	
Turn - on Delay Time	t _{d(on)}		-	36	-	
Rise Time	t _r	$I_C = 50A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	21	-	no
Turn - off Delay Time	$t_{d(off)}$	$T_i = 25^{\circ}C$	-	115	-	ns
Fall Time	t _f	Inductive Load	-	91	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	1	1.46	1	mJ
Turn - off Switching Loss	E _{off}	,	1	1.29	1	
Turn - on Delay Time	t _{d(on)}		-	37	-	_
Rise Time	t _r	$I_C = 50A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	ı	33	•	ns
Turn - off Delay Time	$t_{d(off)}$	$T_i = 175^{\circ}C$	-	145	-	
Fall Time	t _f	Inductive Load	1	147	1	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.97	-	mJ
Turn - off Switching Loss	E _{off}	1000100	-	1.85	-	IIIJ
		$I_C = 150A, V_{CC} = 520V,$				-
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V,$	FULL SQUARE			
		$R_G = 50\Omega, T_j = 175^{\circ}C$				1
Short Circuit Withstand Time	t _{sc}	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 25^{\circ}C$	8	1	1	μs
Short Circuit Withstand Time	t _{sc} *2	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 150$ °C	6	-	-	μs

^{*2} Design assurance without measurement

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• Electrical Characteristic Curves

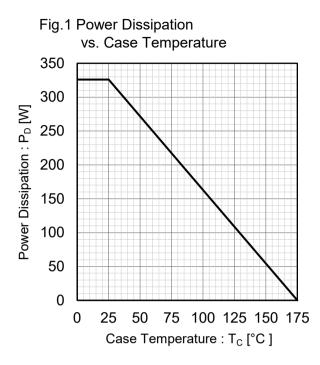


Fig.2 Collector Current vs. Case Temperature

100

80

40 $T_{j \leq 175^{\circ}C}$ $T_{j \leq 15V}$ 0

25

50

75

100

125

150

175

Case Temperature: T_{c} [°C]

Fig.3 Forward Bias Safe Operating Area

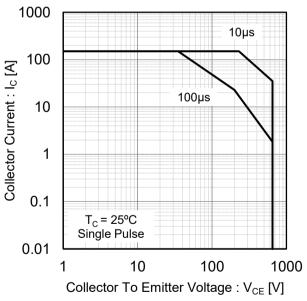
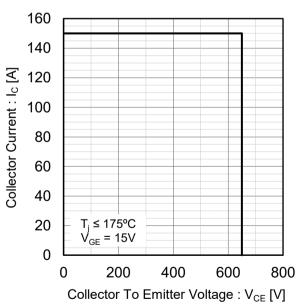


Fig.4 Reverse Bias Safe Operating Area



● Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

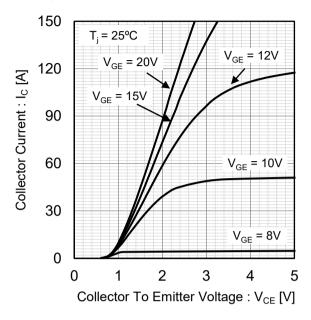


Fig.6 Typical Output Characteristics

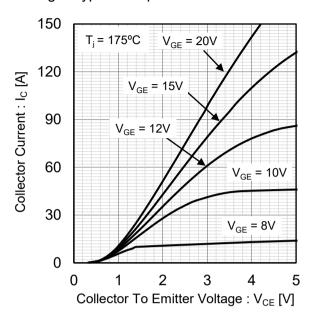


Fig.7 Typical Transfer Characteristics

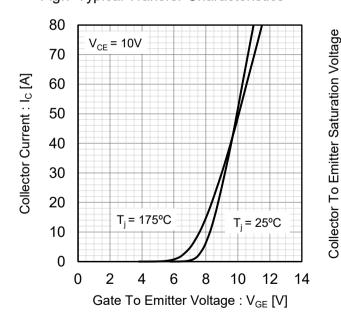
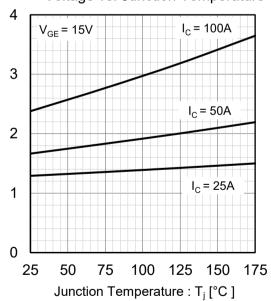


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



: V_{CE(sat)} [V]

0

5

● Electrical Characteristic Curves

Voltage vs. Gate To Emitter Voltage Collector To Emitter Vo

Fig.9 Typical Collector To Emitter Saturation

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

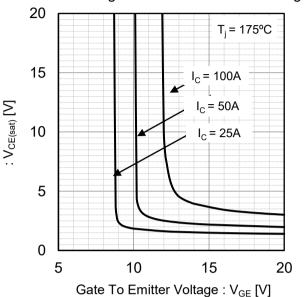


Fig.11 Typical Switching Time vs. Collector Current

10

15

Gate To Emitter Voltage: VGE [V]

20

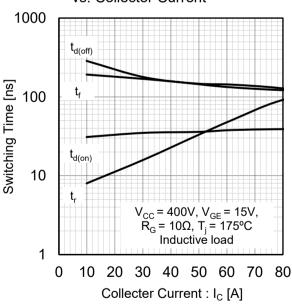
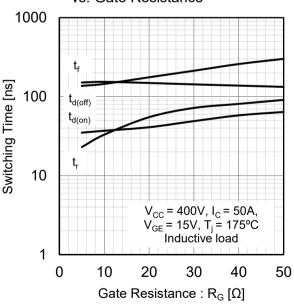


Fig.12 Typical Switching Time vs. Gate Resistance



• Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

10

| Eof | V_{CC} = 400V, V_{GE} = 15V, R_G = 10Ω, T_j = 175°C | Inductive load | O 10 20 30 40 50 60 70 80 | Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] E_{off} 1 0.1 $V_{CC} = 400V, I_C = 50A,$ $V_{GE} = 15V, T_j = 175^{\circ}C$ Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Energy Losses

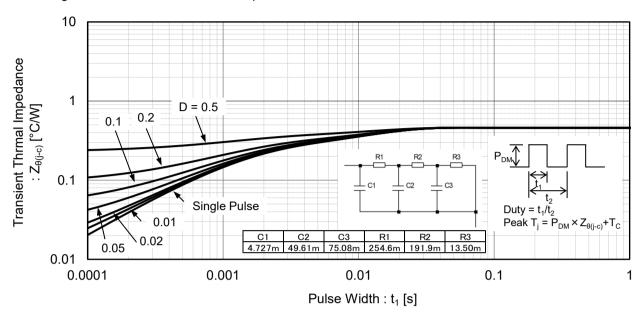
Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 $\boldsymbol{C}_{\text{ies}}$ 1000 Capacitance [pF] C_oes 100 10 C_{res} f = 1MHz $V_{GE} = 0V$ $T_i = 25^{\circ}C$ 1 0.01 0.1 10 100 Collector To Emitter Voltage: V_{CE} [V]

15 V_{CE} = 200V Gate To Emitter Voltage : V_{GE} [V] V_{CE} = 300V 10 V_{CE} = 400V 5 $I_{\rm C} = 50A$ $T_i = 25^{\circ}C$ 0 0 10 20 30 40 50 60 Gate Charge: Qq [nQ]

Fig.16 Typical Gate Charge

• Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

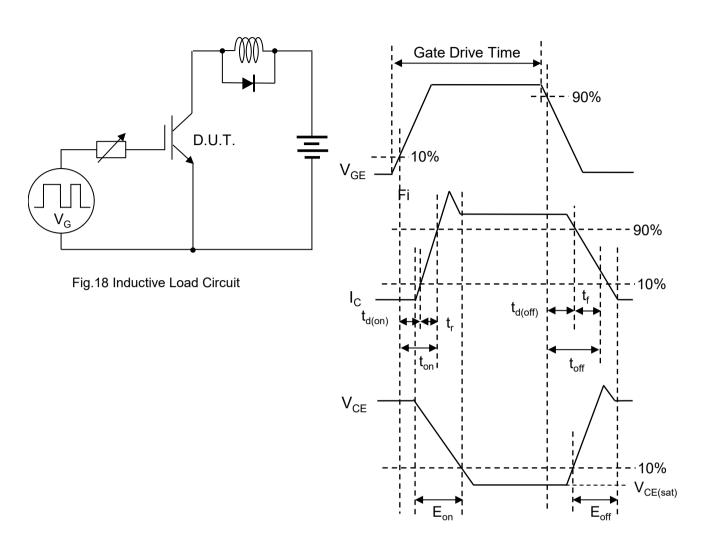


Fig.19 Inductive Load Waveform

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